

DERWENT-ACC-NO: 2002-412432

DERWENT-WEEK: 200275

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TITLE: Method for forming storage electrode of high dielectric capacitor

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PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE	PAGES	MAIN-IPC
KR 2001113317 A	December 28, 2001	N/A	001	H01L 027/105

APPLICATION-DATA:

PUB-NO	APPL-DESCRIPTOR	APPL-NO	APPL-DATE
KR2001113317A	N/A	2000KR-0033610	June 19, 2000

INT-CL (IPC): H01L027/105

ABSTRACTED-PUB-NO: KR2001113317A

BASIC-ABSTRACT:

NOVELTY - A storage electrode formation method is provided to improve an adhesive property between a platinum seed film and an oxide layer by forming an alumina(Al_2O_3) adhesive film on the platinum seed.

DETAILED DESCRIPTION - After forming an interlayer dielectric(21) having a contact hole on a semiconductor substrate(20), a plug(22) is filled into the contact hole. A platinum(Pt) seed(23) is formed on the resultant structure. An alumina(Al_2O_3) adhesive film(24) is formed on the entire surface of the

platinum seed(23). After forming an oxide layer(25) on the alumina adhesive film(24), the oxide layer(25) and the alumina adhesive film(24) are sequentially etched. Platinum is filled into the etched portion by growing the platinum seed. After sequentially removing the remaining oxide layer(25) and alumina adhesive film(24), the exposed platinum seed(23) is then etched.

CHOSEN-DRAWING: Dwg.1/10

TITLE-TERMS: METHOD FORMING STORAGE ELECTRODE HIGH
DIELECTRIC CAPACITOR

DERWENT-CLASS: L03 U11 U12

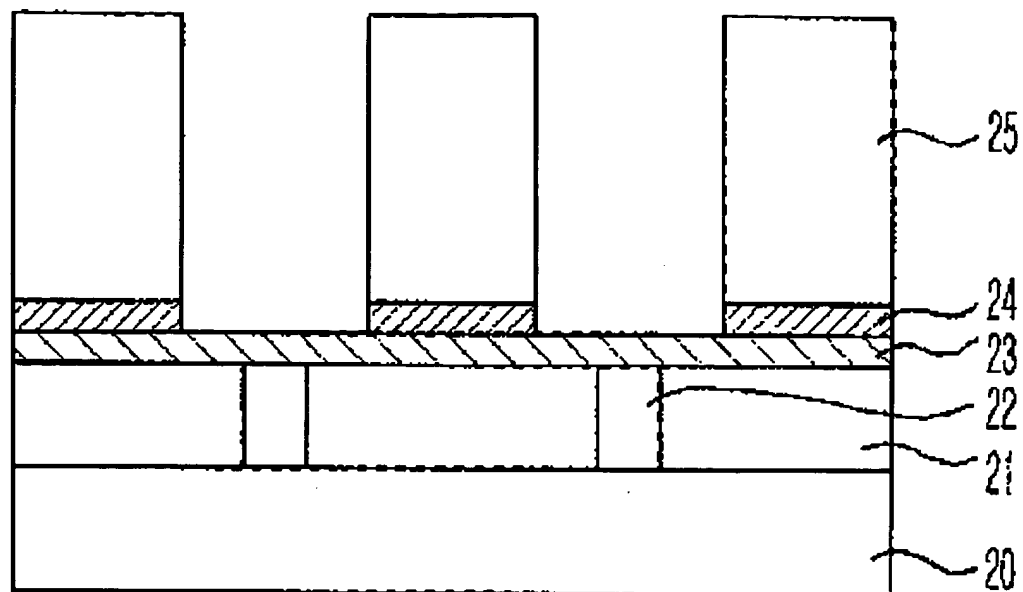
CPI-CODES: L04-C11C2; L04-C12; L04-C13B;

EPI-CODES: U11-C05G1B; U12-C02; U12-Q;

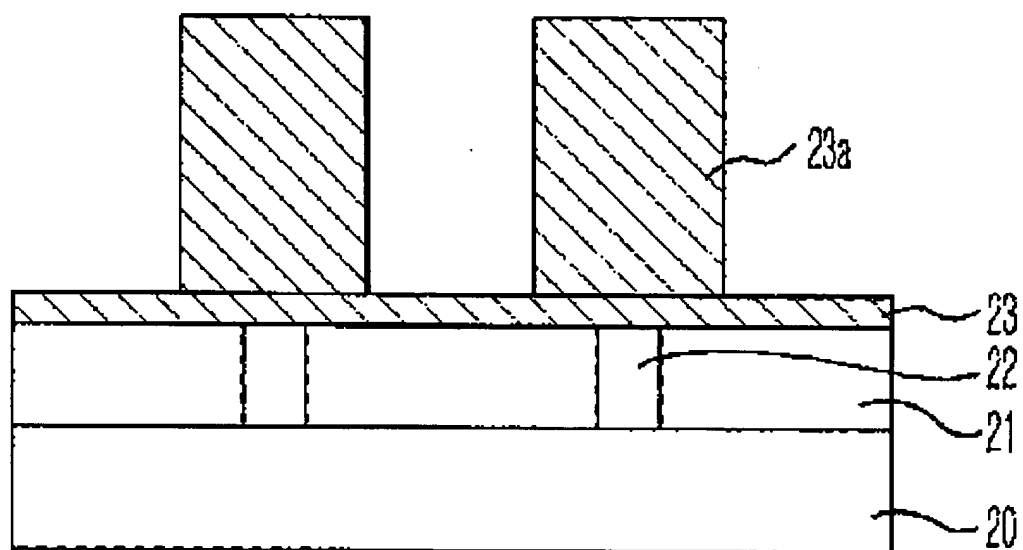
SECONDARY-ACC-NO:

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(a)



(b)



(c)

